



DMP31D0UFB4

30V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	Max R _{DS(ON)}	Max I _D @ T _A = +25°C
	$1\Omega @ V_{GS} = -4.5V$	-0.76A
-30V	1.5Ω @ V _{GS} = -2.5V	-0.62A
	2Ω @ V _{GS} = -1.8V	-0.54A

Description and Applications

This MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Load Switch in portable electronics

Features and Benefits

- Footprint of just 0.6mm² Thirteen Times Smaller than SOT23 .
- 0.4mm Profile Ideal for Low Profile Applications .
- Low Gate Threshold Voltage .
- Fast Switching Speed
- ESD Protected Gate 2KV •
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2) •
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

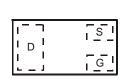
- Case: X2-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe; Solderable per MIL-STD-202, Method 208 @4)
- **Terminal Connections: See Diagram**
- Weight: 0.001 grams (Approximate)



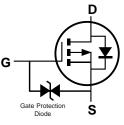


X2-DFN1006-3

Bottom View



Top View Internal Schematic



Equivalent Circuit

Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DMP31D0UFB4-7B	P6	7	8	10,000

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds. 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

Notes:

DMP31D0UFB4-7B



P6 = Product Type Marking Code

Top View Bar Denotes Gate And Source Side



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V _{DSS}	-30	V	
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Drain Current	Steady State	$T_A = +25^{\circ}C$ (Note 6) $T_A = +85^{\circ}C$ (Note 6) $T_A = +25^{\circ}C$ (Note 5)	ID	-0.76 -0.55 -0.54	А
Pulsed Drain Current (Note 7)		IDM	2	А	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

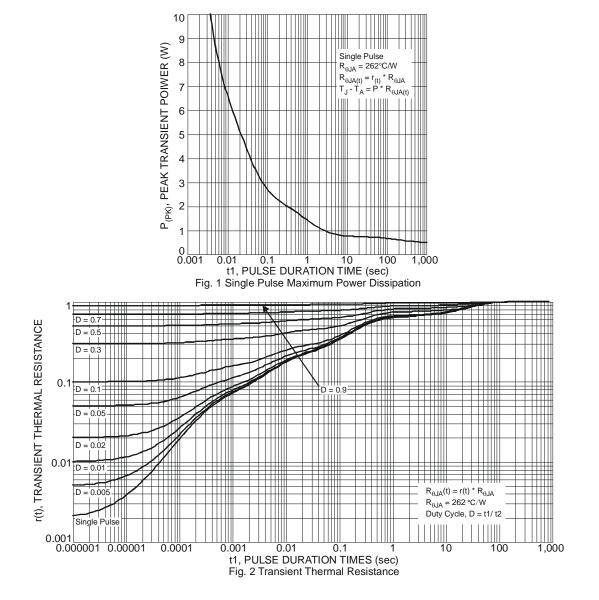
Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 5)		0.46	10/	
Power Dissipation	(Note 6)	PD	0.92	W	
Thermel Desistance Junction to Ambient	(Note 5)	P	271	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	R _{θJA}	136	-C/W	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

Notes:

5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.

7. Device mounted on minimum recommended pad layout test board, 10μ s pulse duty cycle = 1%.



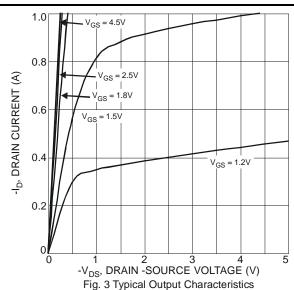


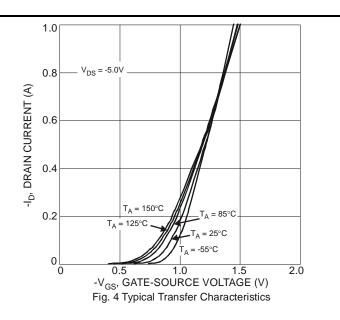
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Мах	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)	Symbol	IVIIII	тур	Wax	onit	Test condition
Drain-Source Breakdown Voltage	BV _{DSS}	-30	-	-	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current $T_J = +25^{\circ}C$	I _{DSS}	-	-	-1	μA	$V_{DS} = -30V, V_{GS} = 0V$
Gate-Source Leakage	IGSS	-	-	±3	μA	$V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)	1000					
Gate Threshold Voltage	V _{GS(TH)}	-0.5	-0.6	-1.1	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
			0.45	1		$V_{GS} = -4.5V, I_{D} = -400mA$
Static Drain-Source On-Resistance	R _{DS(ON)}	-	0.54	1.5	Ω	V _{GS} = -2.5V, I _D = -200mA
	. ,		0.64	2		V _{GS} = -1.8V, I _D = -100mA
Forward Transfer Admittance	Y _{fs}	50	-	-	mS	$V_{DS} = -3V, I_D = -300 \text{mA}$
Diode Forward Voltage	V _{SD}	-	-	-1.2	V	$V_{GS} = 0V, I_{S} = -300mA$
DYNAMIC CHARACTERISTICS (Note9)						
Input Capacitance	Ciss	-	76	150	pF	
Output Capacitance	Coss	-	9	20	pF	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz
Reverse Transfer Capacitance	Crss	-	6.43	15	pF	
Gate Resistance	Rg	-	167	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge	Qg		0.9	-	nC	V _{GS} = -4.5V, V _{DS} = -15V,I _D = -1A
Total Gate Charge	Qg	-	1.5	-	nC	
Gate-Source Charge	Q _{qs}	-	0.1	-	nC	V _{GS} = -8V, V _{DS} = -15V, I _D = -1A
Gate-Drain Charge	Q _{qd}	-	0.2	-	nC	
Turn-On Delay Time	t _{D(ON)}	-	4.98	-	ns	
Turn-On Rise Time	t _R	-	5.85	-	ns	$V_{DD} = -10V, R_{L} = 10\Omega$
Turn-Off Delay Time	t _{D(OFF)}	-	35.7	-	ns	$V_{GS} = -4.5V, R_g = 6\Omega$
Turn-Off Fall Time	tF	-	16.6	-	ns	

Notes: 8. Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to product testing.

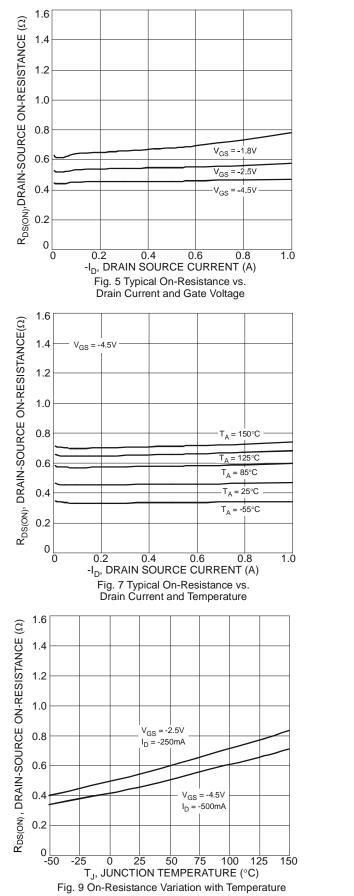


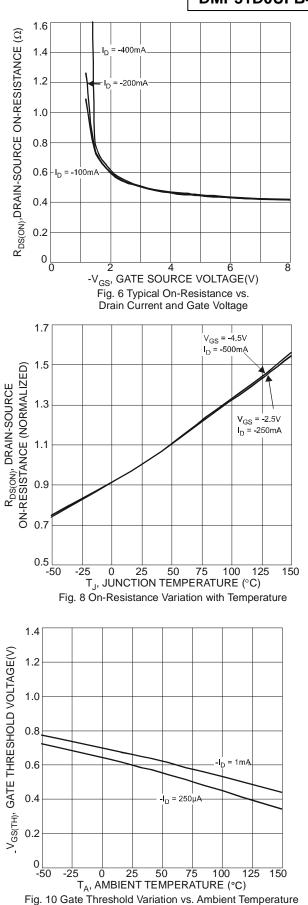


Typical Electrical Characteristics



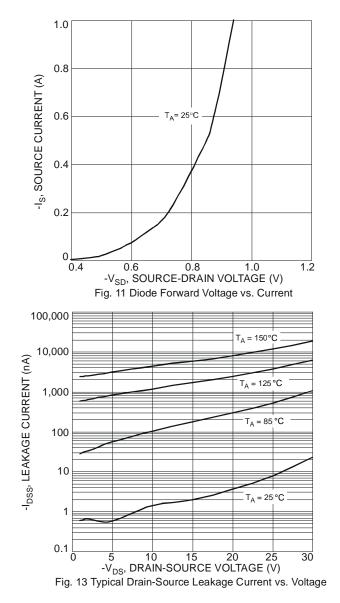
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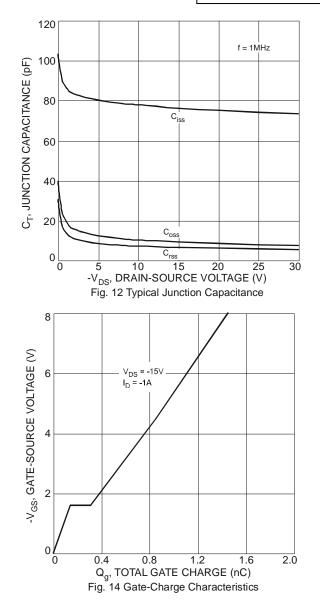






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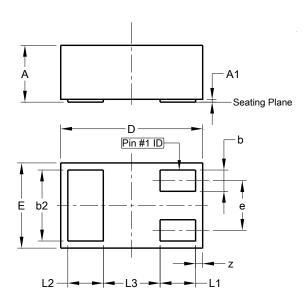






Package Outline Dimensions

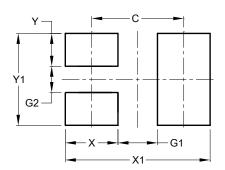
Please see http://www.diodes.com/package-outlines.html for the latest version.



X2-DFN1006-3						
Dim	Min	Max	Тур			
Α		0.40				
A1	0.00	0.05	0.03			
b	0.10	0.20	0.15			
b2	0.45	0.55	0.50			
D	0.95	1.05	1.00			
Е	0.55	0.65	0.60			
е	-	-	0.35			
L1	0.20	0.30	0.25			
L2	0.20	0.30	0.25			
L3	-	-	0.40			
z	0.02	0.08	0.05			
All	All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



X2-DFN1006-3

X2-DFN1006-3

Dimensions	Value (in mm)
С	0.70
G1	0.30
G2	0.20
Х	0.40
X1	1.10
Y	0.25
Y1	0.70



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